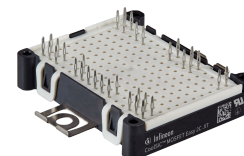


Final datasheet

EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / pre-applied thermal interface material / NTC

Features

- Electrical features
 - $V_{DS} = 1200\text{ V}$
 - $I_{DN} = 75\text{ A} / I_{DRM} = 150\text{ A}$
 - Low inductive design
 - Low switching losses
 - High current density
 - Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>
- Mechanical features
 - PressFIT contact technology
 - Integrated NTC temperature sensor
 - Rugged mounting due to integrated mounting clamps
 - Package with CTI > 600
 - High current pin



Potential applications

- High-frequency switching application
- DC/DC converter
- DC charger for EV

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

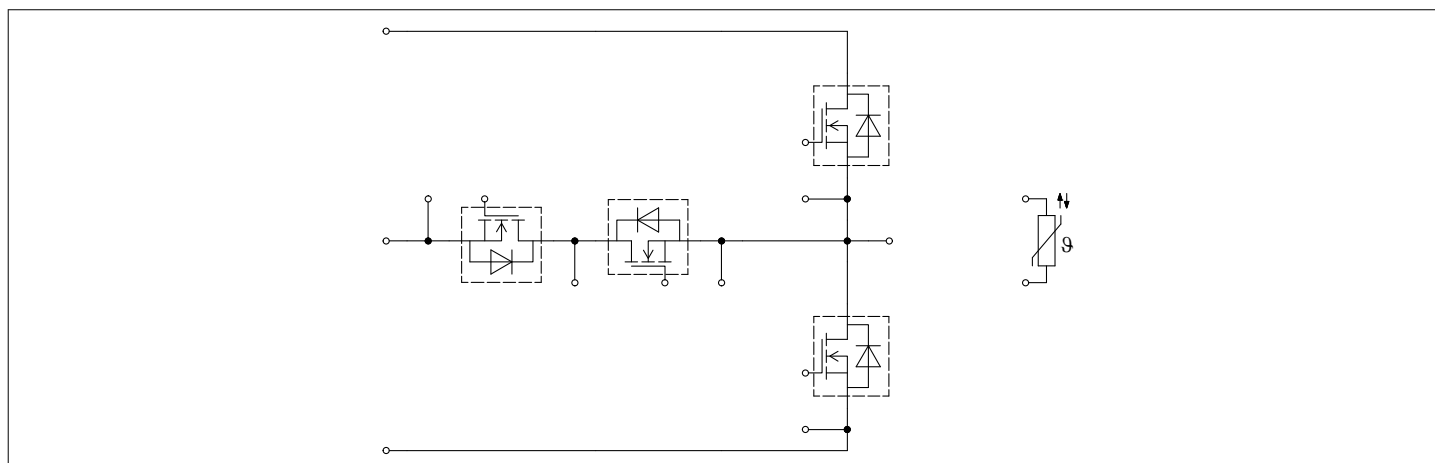


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	4.0	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	CTI		> 600	
Relative thermal index (electrical)	RTI	frame	180	°C
		lid	150	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			19		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25 \text{ °C}$, per switch		2.6		mΩ
Storage temperature	T_{stg}		-40		150	°C
Maximum baseplate operation temperature	T_{BPmax}				150	°C
Mounting force per clamp	F		40		80	N
Weight	G			38		g

Note: The current up to 50 A per pin is limited by the interaction of the pins with the PCB design and cooling conditions.

Storage and shipment of modules with TIM => see AN 2012-07

2 MOSFET, T1 / T2

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		$T_{vj} = 25 \text{ °C}$	1200	V
Implemented drain current	I_{DN}			75	A
Continuous DC drain current	I_{DDC}	$T_{vj} = 175 \text{ °C}$, $V_{GS} = 18 \text{ V}$	$T_H = 25 \text{ °C}$	95	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		150	A
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$		-10/25	V

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. static voltage	V_{GS}		-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 75\text{ A}$	$V_{GS} = 15\text{ V}, T_{vj} = 25\text{ °C}$		10		mΩ
			$V_{GS} = 18\text{ V}, T_{vj} = 25\text{ °C}$		8.3	12.8	
			$V_{GS} = 18\text{ V}, T_{vj} = 125\text{ °C}$		13		
			$V_{GS} = 18\text{ V}, T_{vj} = 175\text{ °C}$		16.8		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 33\text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25\text{ °C},$ (tested after 1ms pulse at $V_{GS} = +20\text{ V}$), $T_{vj} = 25\text{ °C}$		3.45	4.3	5.15	V
Total gate charge	Q_G	$V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			0.237		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$			3.5		Ω
Input capacitance	C_{ISS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		7.21		nF
Output capacitance	C_{OSS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.293		nF
Reverse transfer capacitance	C_{rss}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.02		nF
C_{OSS} stored energy	E_{OSS}	$V_{DS} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			121		μJ
Drain-source leakage current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		0.3	296	μA
Gate-source leakage current	I_{GSS}	$V_{DS} = 0\text{ V}, T_{vj} = 25\text{ °C}$	$V_{GS} = 20\text{ V}$			400	nA
Turn-on delay time (inductive load)	$t_{d\ on}$	$I_D = 75\text{ A}, R_{Gon} = 10\text{ Ω}, V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, t_{dead} = 1000\text{ ns}, 0.1\text{ }V_{GS}$ to $0.1\text{ }I_D$	$T_{vj} = 25\text{ °C}$		50.4		ns
			$T_{vj} = 125\text{ °C}$		45.7		
			$T_{vj} = 175\text{ °C}$		43.8		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time (inductive load)	t_r	$I_D = 75 \text{ A}$, $R_{Gon} = 10 \text{ } \Omega$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3/18 \text{ V}$, $t_{dead} = 1000 \text{ ns}$, $0.1 I_D$ to $0.9 I_D$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	24.5		ns
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	22.1		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	21.5		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 75 \text{ A}$, $R_{Goff} = 2.7 \text{ } \Omega$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3/18 \text{ V}$, $0.9 V_{GS}$ to $0.9 I_D$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	63		ns
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	71.4		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	76.4		
Fall time (inductive load)	t_f	$I_D = 75 \text{ A}$, $R_{Goff} = 2.7 \text{ } \Omega$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3/18 \text{ V}$, $0.9 I_D$ to $0.1 I_D$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	28.7		ns
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	31		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	32.5		
Turn-on energy loss per pulse	E_{on}	$I_D = 75 \text{ A}$, $V_{DD} = 800 \text{ V}$, $L_\sigma = 15 \text{ nH}$, $V_{GS} = -3/18 \text{ V}$, $R_{Gon} = 10 \text{ } \Omega$, $di/dt =$ $4.11 \text{ kA}/\mu\text{s}$ ($T_{vj} = 175 \text{ } ^\circ\text{C}$), $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	2.57		mJ
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	2.74		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	2.94		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	$I_D = 75 \text{ A}$, $V_{DD} = 800 \text{ V}$, $L_\sigma = 15 \text{ nH}$, $V_{GS} = -3/18 \text{ V}$, $R_{Gon,o} = 1 \text{ } \Omega$, $di/dt =$ $10.6 \text{ kA}/\mu\text{s}$ ($T_{vj} = 175 \text{ } ^\circ\text{C}$), $t_{dead} = 100 \text{ ns}$	$T_{vj} = 25 \text{ } ^\circ\text{C}$	1.01		mJ
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	1.11		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	1.27		
Turn-off energy loss per pulse	E_{off}	$I_D = 75 \text{ A}$, $V_{DD} = 800 \text{ V}$, $L_\sigma = 15 \text{ nH}$, $V_{GS} = -3/18 \text{ V}$, $R_{Goff} = 2.7 \text{ } \Omega$, $dv/dt = 28.2$ $\text{kV}/\mu\text{s}$ ($T_{vj} = 175 \text{ } ^\circ\text{C}$)	$T_{vj} = 25 \text{ } ^\circ\text{C}$	0.8		mJ
			$T_{vj} = 125 \text{ } ^\circ\text{C}$	0.86		
			$T_{vj} = 175 \text{ } ^\circ\text{C}$	0.91		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material		0.62		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ\text{C}$
Temperature under overload switching conditions	$T_{vj\ over}$	Overload, cumulative max. 100 h			200	$^\circ\text{C}$

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.

3 Body diode (MOSFET, T1 / T2)

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	$T_{vj} = 175\text{ °C}$, $V_{GS} = -3\text{ V}$	$T_H = 25\text{ °C}$	55	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD} = 75\text{ A}$, $V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$	4.35	5.35	V
			$T_{vj} = 125\text{ °C}$	4.05		
			$T_{vj} = 175\text{ °C}$	3.9		
Peak reverse recovery current	I_{rrm}	$I_{SD} = 75\text{ A}$, $di_s/dt = 4.11\text{ kA}/\mu\text{s}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3\text{ V}$, $t_{dead} = 1000\text{ ns}$	$T_{vj} = 25\text{ °C}$	35.2		A
			$T_{vj} = 125\text{ °C}$	50		
			$T_{vj} = 175\text{ °C}$	61.5		
Recovered charge	Q_{rr}	$I_{SD} = 75\text{ A}$, $di_s/dt = 4.11\text{ kA}/\mu\text{s}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3\text{ V}$, $t_{dead} = 1000\text{ ns}$	$T_{vj} = 25\text{ °C}$	0.51		μC
			$T_{vj} = 125\text{ °C}$	1.12		
			$T_{vj} = 175\text{ °C}$	1.59		
Reverse recovery energy	E_{rec}	$I_{SD} = 75\text{ A}$, $di_s/dt = 4.11\text{ kA}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$), $V_{DD} = 800\text{ V}$, $V_{GS} = -3\text{ V}$, $t_{dead} = 1000\text{ ns}$	$T_{vj} = 25\text{ °C}$	0.13		mJ
			$T_{vj} = 125\text{ °C}$	0.34		
			$T_{vj} = 175\text{ °C}$	0.5		
Reverse recovery energy, optimized	$E_{rec,o}$	$I_{SD} = 75\text{ A}$, $di_s/dt = 10.6\text{ kA}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$), $V_{DD} = 800\text{ V}$, $V_{GS} = -3\text{ V}$, $t_{dead} = 100\text{ ns}$	$T_{vj} = 25\text{ °C}$	0.89		mJ
			$T_{vj} = 125\text{ °C}$	1.73		
			$T_{vj} = 175\text{ °C}$	2.6		

4 MOSFET, T3 / T4

Table 8 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		$T_{vj} = 25\text{ °C}$	1200	V
Implemented drain current	I_{DN}			75	A
Continuous DC drain current	I_{DDC}	$T_{vj} = 175\text{ °C}$, $V_{GS} = 18\text{ V}$	$T_H = 25\text{ °C}$	85	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		150	A
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$		-10/25	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 9 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 75\text{ A}$	$V_{GS} = 15\text{ V}, T_{vj} = 25\text{ °C}$		10		mΩ
			$V_{GS} = 18\text{ V}, T_{vj} = 25\text{ °C}$		8.3	12.8	
			$V_{GS} = 18\text{ V}, T_{vj} = 125\text{ °C}$		13		
			$V_{GS} = 18\text{ V}, T_{vj} = 175\text{ °C}$		16.8		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 33\text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25\text{ °C},$ (tested after 1ms pulse at $V_{GS} = +20\text{ V}$), $T_{vj} = 25\text{ °C}$		3.45	4.3	5.15	V
Total gate charge	Q_G	$V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			0.237		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$			3.5		Ω
Input capacitance	C_{ISS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		7.21		nF
Output capacitance	C_{OSS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.293		nF
Reverse transfer capacitance	C_{rss}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.02		nF
C_{OSS} stored energy	E_{OSS}	$V_{DS} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			121		μJ
Drain-source leakage current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		0.3	296	μA
Gate-source leakage current	I_{GSS}	$V_{DS} = 0\text{ V}, T_{vj} = 25\text{ °C}$	$V_{GS} = 20\text{ V}$			400	nA
Turn-on delay time (inductive load)	$t_{d on}$	$I_D = 75\text{ A}, R_{Gon} = 5.6\text{ Ω}, V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, t_{dead} = 1000\text{ ns}, 0.1 V_{GS}$ to $0.1 I_D$	$T_{vj} = 25\text{ °C}$		46		ns
			$T_{vj} = 125\text{ °C}$		42.9		
			$T_{vj} = 175\text{ °C}$		41.1		
Rise time (inductive load)	t_r	$I_D = 75\text{ A}, R_{Gon} = 5.6\text{ Ω}, V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, t_{dead} = 1000\text{ ns}, 0.1 I_D$ to $0.9 I_D$	$T_{vj} = 25\text{ °C}$		19.9		ns
			$T_{vj} = 125\text{ °C}$		17.8		
			$T_{vj} = 175\text{ °C}$		17.1		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 75\text{ A}$, $R_{Goff} = 2.7\ \Omega$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$, $0.9\ V_{GS}$ to $0.9\ I_D$	$T_{vj} = 25\ ^\circ\text{C}$	64.1		ns
			$T_{vj} = 125\ ^\circ\text{C}$	73.5		
			$T_{vj} = 175\ ^\circ\text{C}$	79.2		
Fall time (inductive load)	t_f	$I_D = 75\text{ A}$, $R_{Goff} = 2.7\ \Omega$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$, $0.9\ I_D$ to $0.1\ I_D$	$T_{vj} = 25\ ^\circ\text{C}$	30.7		ns
			$T_{vj} = 125\ ^\circ\text{C}$	31.9		
			$T_{vj} = 175\ ^\circ\text{C}$	32.3		
Turn-on energy loss per pulse	E_{on}	$I_D = 75\text{ A}$, $V_{DD} = 800\text{ V}$, $L_\sigma = 15\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Gon} = 5.6\ \Omega$, $di/dt =$ $4.95\text{ kA}/\mu\text{s}$ ($T_{vj} = 175\ ^\circ\text{C}$), $t_{dead} = 1000\text{ ns}$	$T_{vj} = 25\ ^\circ\text{C}$	2.02		mJ
			$T_{vj} = 125\ ^\circ\text{C}$	2.19		
			$T_{vj} = 175\ ^\circ\text{C}$	2.43		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	$I_D = 75\text{ A}$, $V_{DD} = 800\text{ V}$, $L_\sigma = 15\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Gon,o} = 0\ \Omega$, $di/dt =$ $11.1\text{ kA}/\mu\text{s}$ ($T_{vj} = 175\ ^\circ\text{C}$), $t_{dead} = 100\text{ ns}$	$T_{vj} = 25\ ^\circ\text{C}$	0.81		mJ
			$T_{vj} = 125\ ^\circ\text{C}$	0.85		
			$T_{vj} = 175\ ^\circ\text{C}$	0.99		
Turn-off energy loss per pulse	E_{off}	$I_D = 75\text{ A}$, $V_{DD} = 800\text{ V}$, $L_\sigma = 15\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Goff} = 2.7\ \Omega$, $dv/dt = 25.8$ $\text{kV}/\mu\text{s}$ ($T_{vj} = 175\ ^\circ\text{C}$)	$T_{vj} = 25\ ^\circ\text{C}$	0.83		mJ
			$T_{vj} = 125\ ^\circ\text{C}$	0.92		
			$T_{vj} = 175\ ^\circ\text{C}$	0.98		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material		0.78		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ\text{C}$
Temperature under overload switching conditions	$T_{vj\ over}$	Overload, cumulative max. 100 h			200	$^\circ\text{C}$

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.

5 Body diode (MOSFET, T3 / T4)

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	$T_{vj} = 175\ ^\circ\text{C}$, $V_{GS} = -3\text{ V}$	$T_H = 25\ ^\circ\text{C}$	45	A

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD} = 75 \text{ A}$, $V_{GS} = -3 \text{ V}$	$T_{vj} = 25 \text{ °C}$	4.35	5.35	V
			$T_{vj} = 125 \text{ °C}$	4.05		
			$T_{vj} = 175 \text{ °C}$	3.9		
Peak reverse recovery current	I_{rrm}	$I_{SD} = 75 \text{ A}$, $di_s/dt = 4.95 \text{ kA}/\mu\text{s}$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ °C}$	40.7		A
			$T_{vj} = 125 \text{ °C}$	58.1		
			$T_{vj} = 175 \text{ °C}$	70.5		
Recovered charge	Q_{rr}	$I_{SD} = 75 \text{ A}$, $di_s/dt = 4.95 \text{ kA}/\mu\text{s}$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ °C}$	0.55		μC
			$T_{vj} = 125 \text{ °C}$	1.18		
			$T_{vj} = 175 \text{ °C}$	1.61		
Reverse recovery energy	E_{rec}	$I_{SD} = 75 \text{ A}$, $di_s/dt = 4.95 \text{ kA}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$), $V_{DD} = 800 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ °C}$	0.14		mJ
			$T_{vj} = 125 \text{ °C}$	0.37		
			$T_{vj} = 175 \text{ °C}$	0.49		
Reverse recovery energy, optimized	$E_{rec,o}$	$I_{SD} = 75 \text{ A}$, $di_s/dt = 11.1 \text{ kA}/\mu\text{s}$ ($T_{vj} = 175 \text{ °C}$), $V_{DD} = 800 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 100 \text{ ns}$	$T_{vj} = 25 \text{ °C}$	0.88		mJ
			$T_{vj} = 125 \text{ °C}$	1.47		
			$T_{vj} = 175 \text{ °C}$	1.92		

6 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ °C}$, $R_{100} = 493 \text{ }\Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

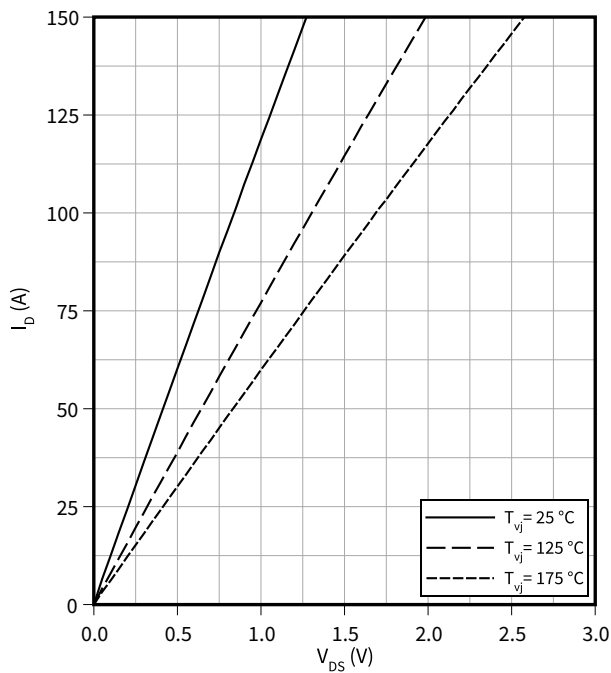
Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4

7 Characteristics diagrams

Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

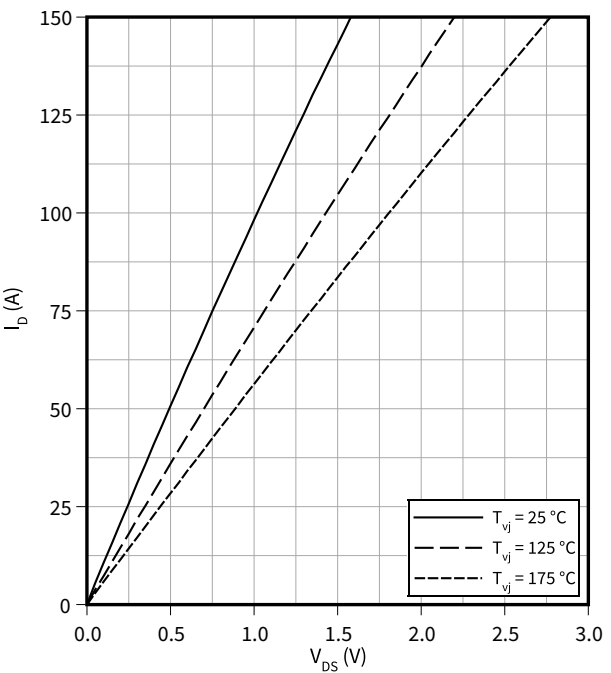
$V_{GS} = 18\text{ V}$



Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

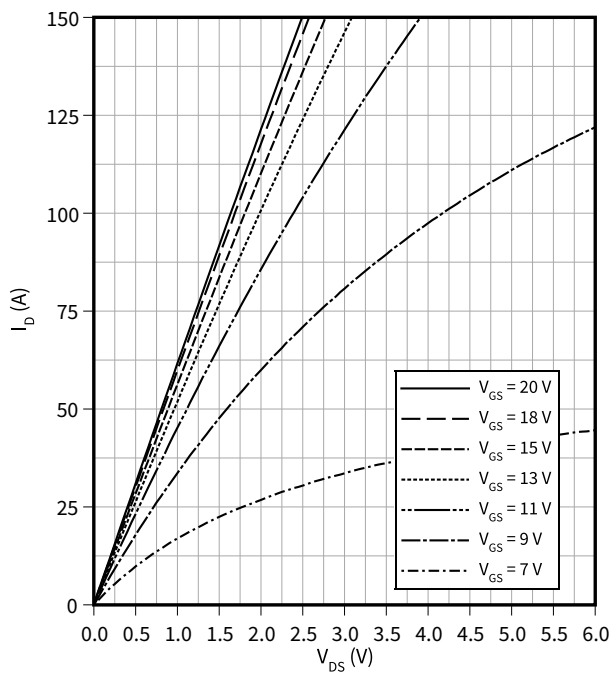
$V_{GS} = 15\text{ V}$



Output characteristic field (typical), MOSFET, T1 / T2

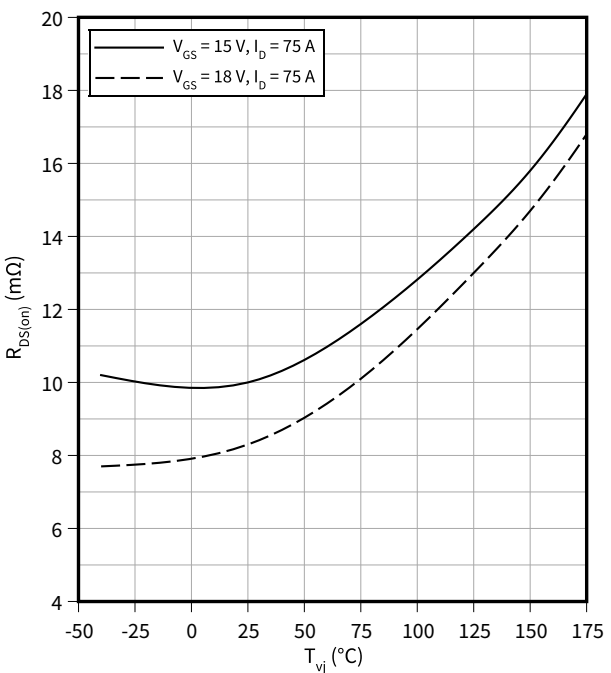
$I_D = f(V_{DS})$

$T_{vj} = 175\text{ °C}$



Drain source on-resistance (typical), MOSFET, T1 / T2

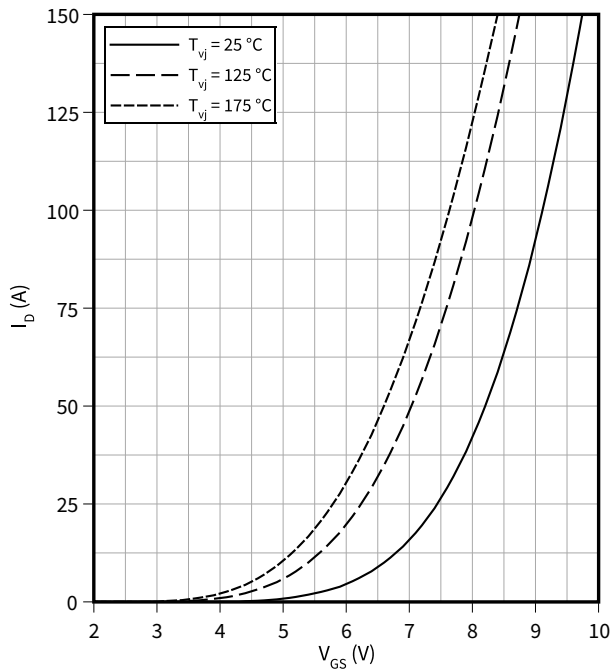
$R_{DS(on)} = f(T_{vj})$



7 Characteristics diagrams

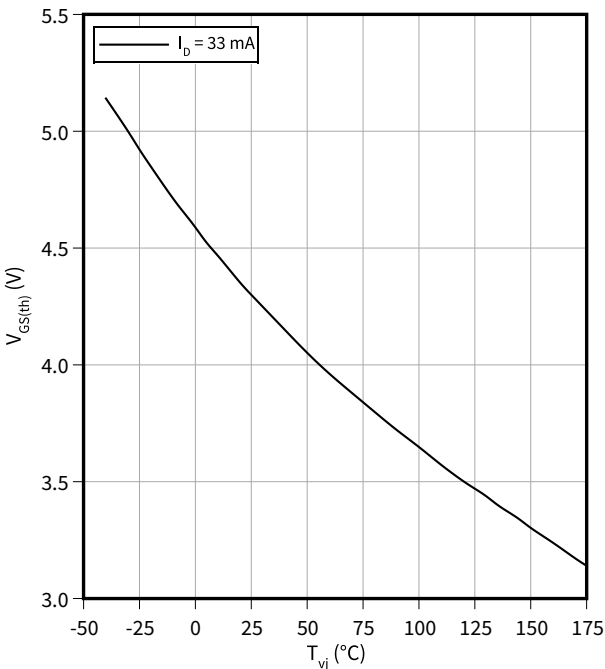
Transfer characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$



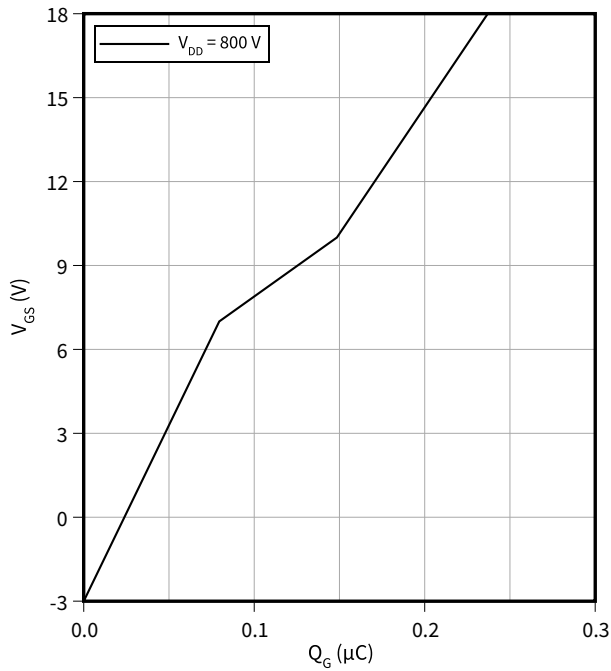
Gate-source threshold voltage (typical), MOSFET, T1 / T2

$V_{GS(th)} = f(T_{vj})$
 $V_{GS} = V_{DS}$



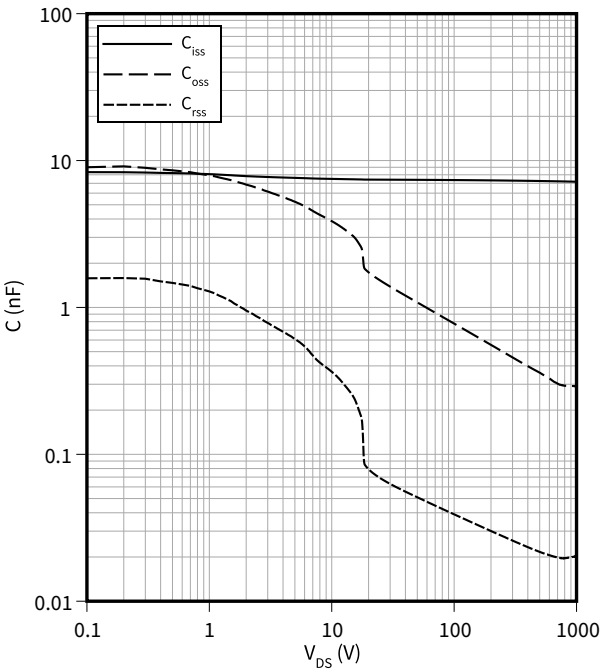
Gate charge characteristic (typical), MOSFET, T1 / T2

$V_{GS} = f(Q_G)$
 $I_D = 75\text{ A}$, $T_{vj} = 25\text{ °C}$



Capacity characteristic (typical), MOSFET, T1 / T2

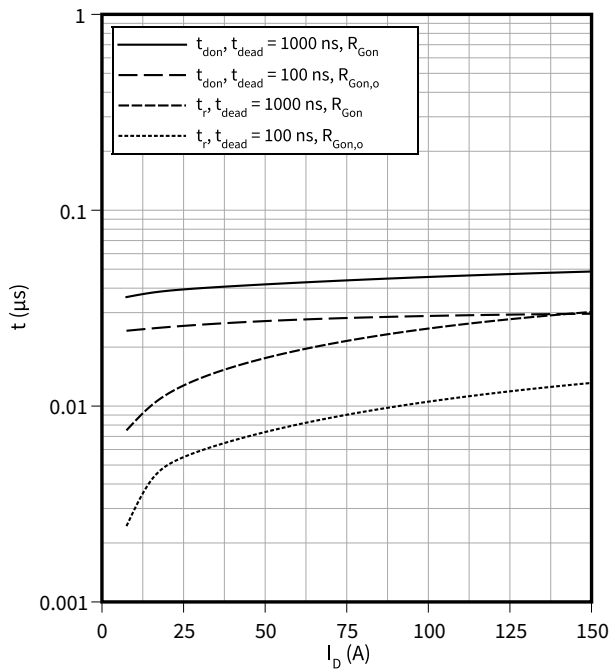
$C = f(V_{DS})$
 $f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$, $V_{GS} = 0\text{ V}$



7 Characteristics diagrams

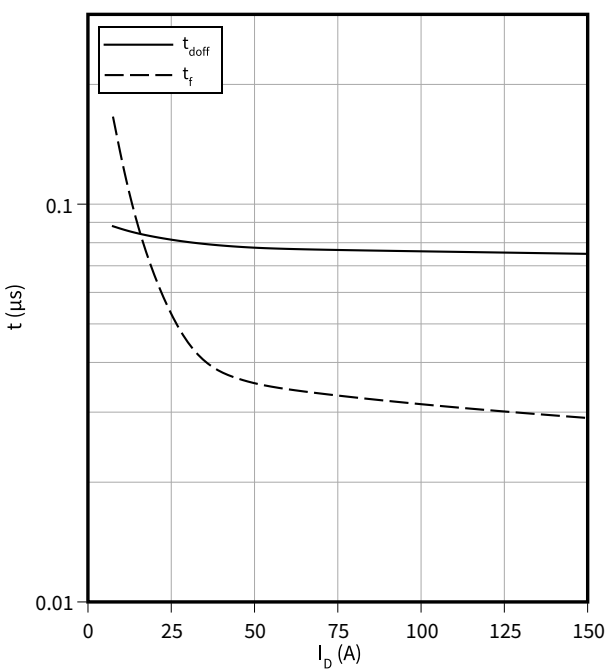
Switching times (typical), MOSFET, T1 / T2

$t = f(I_D)$
 $V_{DD} = 800\text{ V}$, $R_{Gon} = 10\ \Omega$, $R_{Gon,o} = 1\ \Omega$, $T_{vj} = 175\text{ }^\circ\text{C}$,
 $V_{GS} = -3/18\text{ V}$



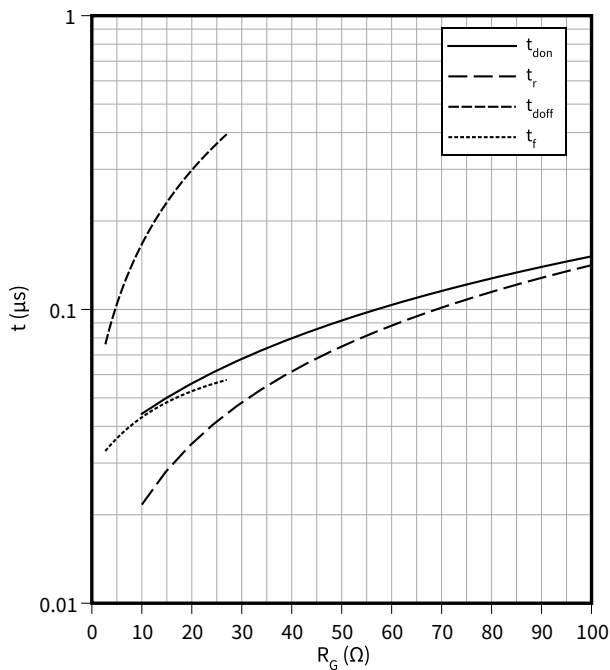
Switching times (typical), MOSFET, T1 / T2

$t = f(I_D)$
 $R_{Goff} = 2.7\ \Omega$, $V_{DD} = 800\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



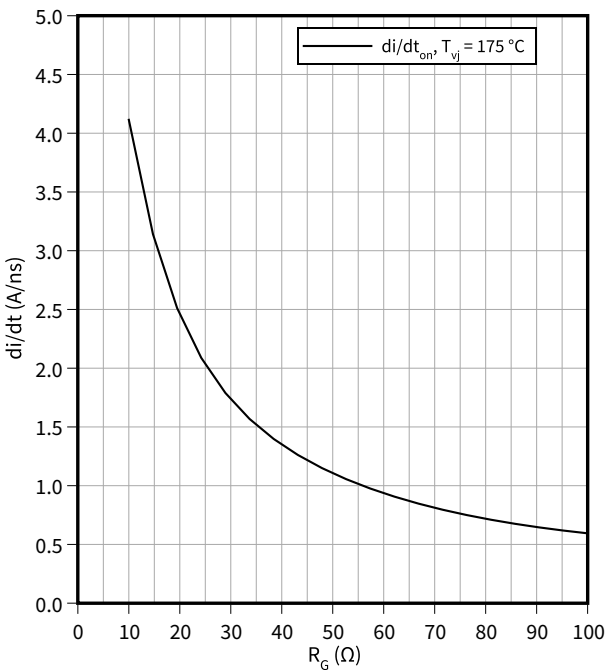
Switching times (typical), MOSFET, T1 / T2

$t = f(R_G)$
 $V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $T_{vj} = 175\text{ }^\circ\text{C}$,
 $V_{GS} = -3/18\text{ V}$



Current slope (typical), MOSFET, T1 / T2

$di/dt = f(R_G)$
 $V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$

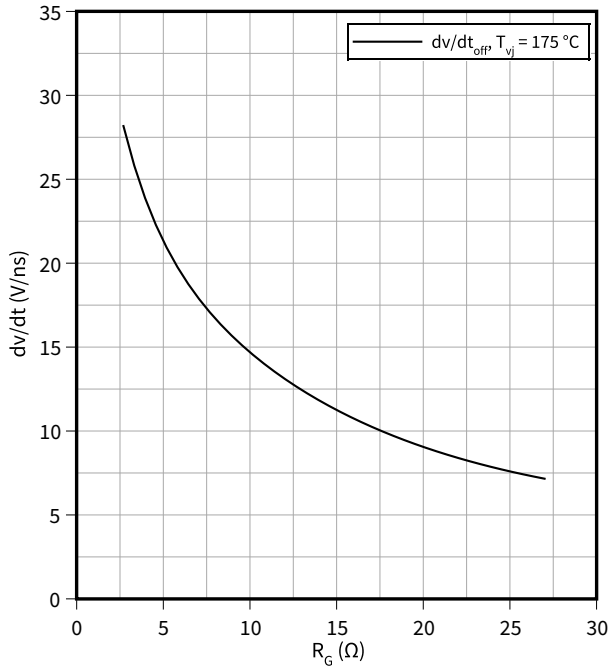


7 Characteristics diagrams

Voltage slope (typical), MOSFET, T1 / T2

$dv/dt = f(R_G)$

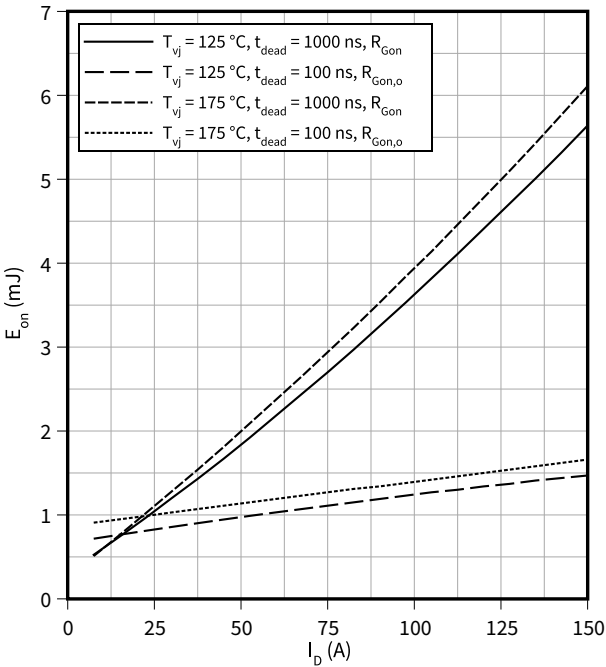
$V_{DD} = 800\text{ V}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(I_D)$

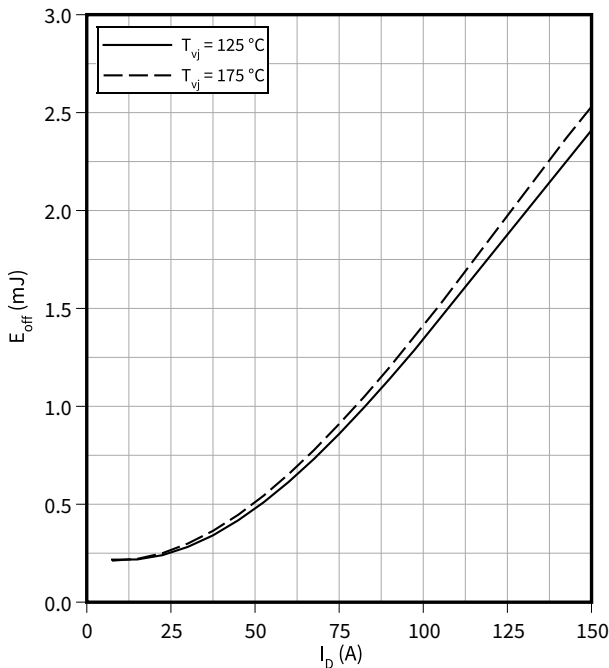
$V_{DD} = 800\text{ V}$, $R_{Gon} = 10\text{ }\Omega$, $R_{Gon,o} = 1\text{ }\Omega$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T1 / T2

$E_{off} = f(I_D)$

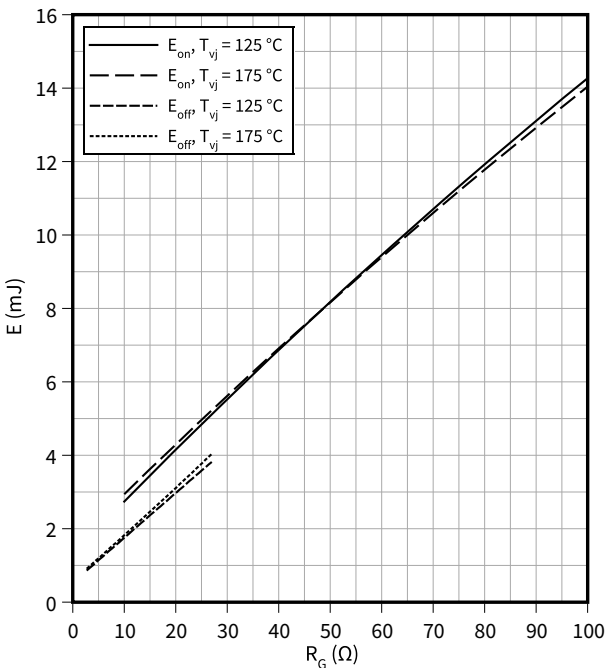
$R_{Goff} = 2.7\text{ }\Omega$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T1 / T2

$E = f(R_G)$

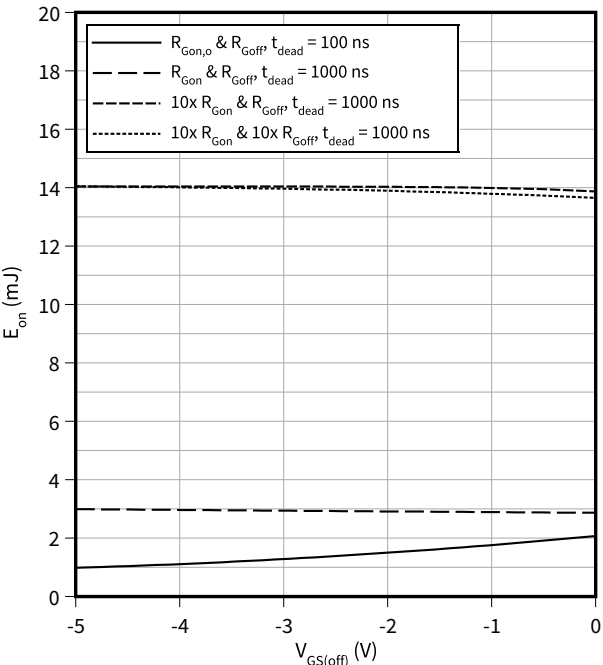
$V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$



7 Characteristics diagrams

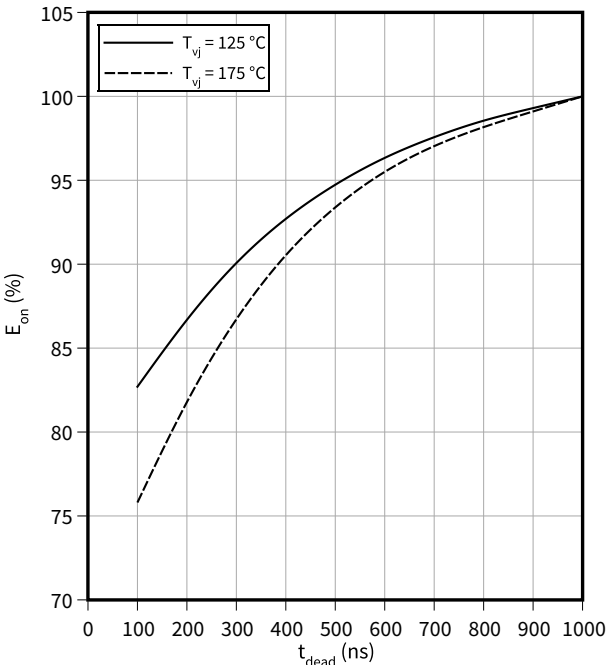
Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(V_{GS(off)})$
 $R_{Goff} = 2.7 \Omega$, $V_{DD} = 800 \text{ V}$, $R_{Gon} = 10 \Omega$, $V_{GS(on)} = 18 \text{ V}$,
 $I_D = 75 \text{ A}$, $R_{Gon,0} = 1 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$



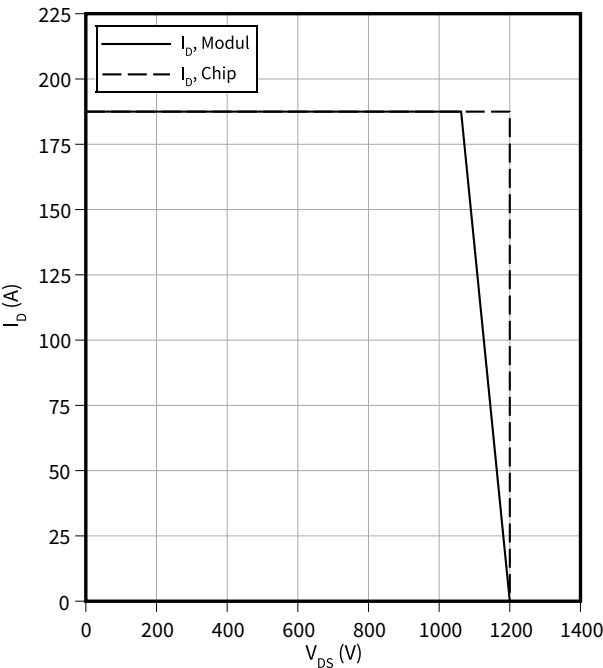
Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(t_{dead})$
 $R_{Gon} = 10 \Omega$, $I_D = 75 \text{ A}$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3/18 \text{ V}$



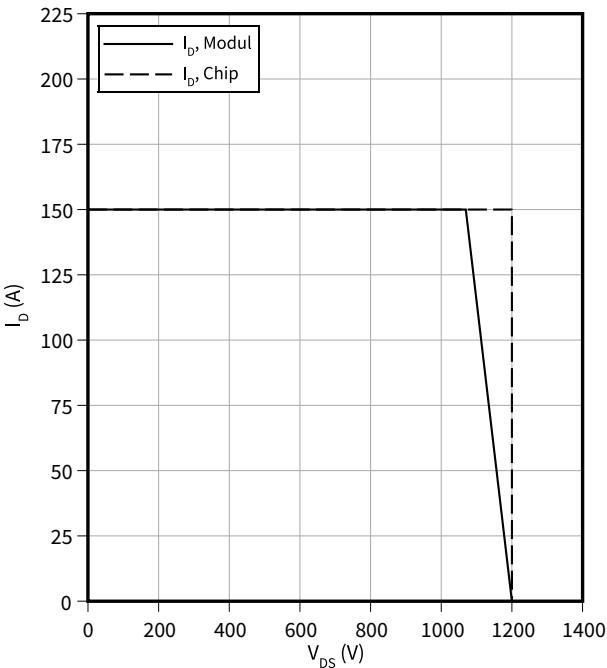
Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

$I_D = f(V_{DS})$
 $R_{Goff} = 3.3 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GS} = -3/18 \text{ V}$



Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

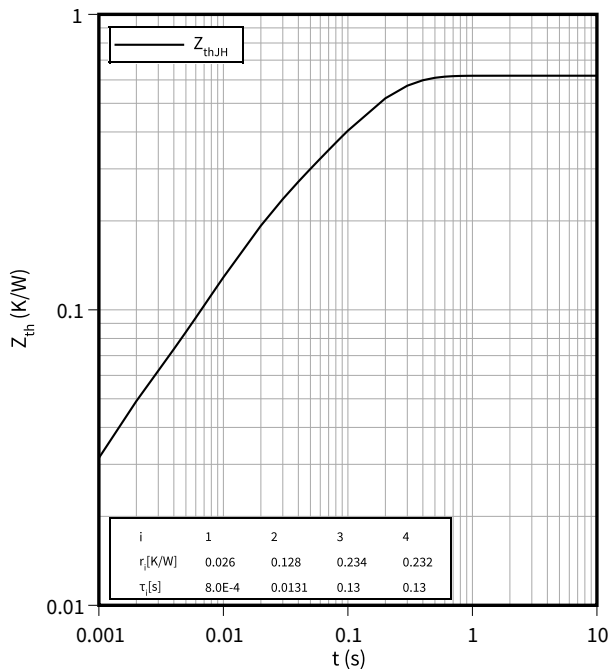
$I_D = f(V_{DS})$
 $R_{Goff} = 2.7 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GS} = -3/18 \text{ V}$



7 Characteristics diagrams

Transient thermal impedance, MOSFET, T1 / T2

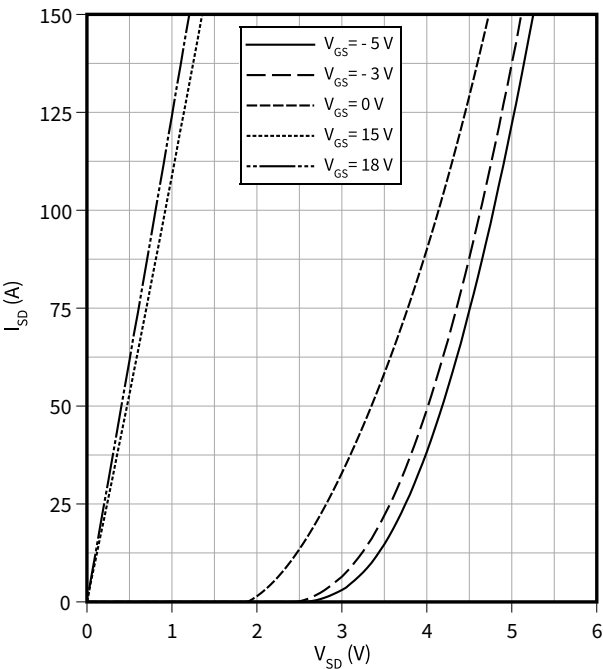
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T1 / T2

$I_{SD} = f(V_{SD})$

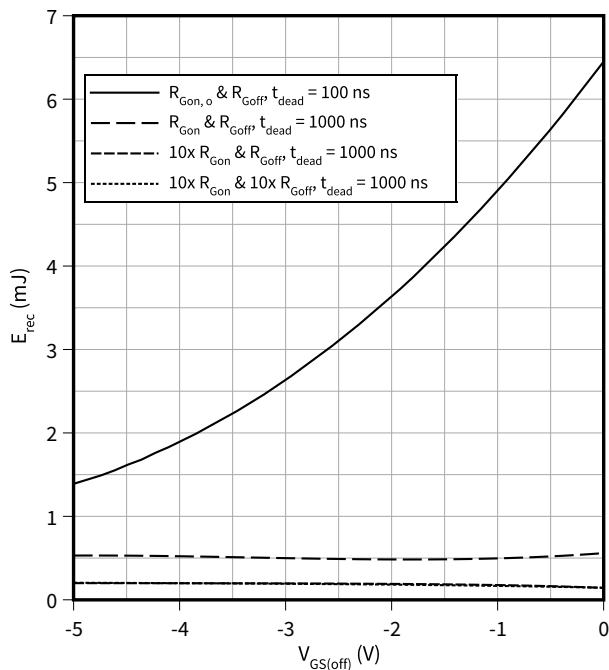
$T_{vj} = 25\text{ }^{\circ}\text{C}$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(V_{GS(off)})$

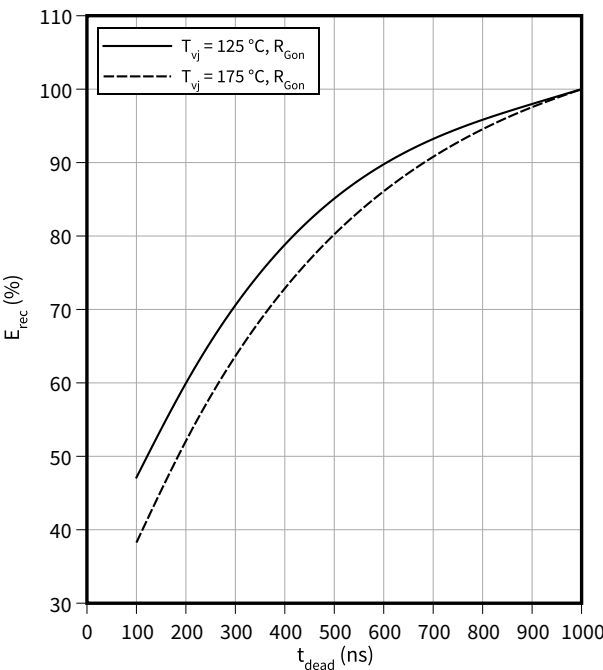
$R_{Goff} = 2.7\text{ }\Omega$, $R_{Gon} = 10\text{ }\Omega$, $V_{GS(on)} = 18\text{ V}$, $I_{SD} = 75\text{ A}$,
 $R_{Gon,o} = 1\text{ }\Omega$, $V_{DD} = 800\text{ V}$, $T_{vj} = 175\text{ }^{\circ}\text{C}$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(t_{dead})$

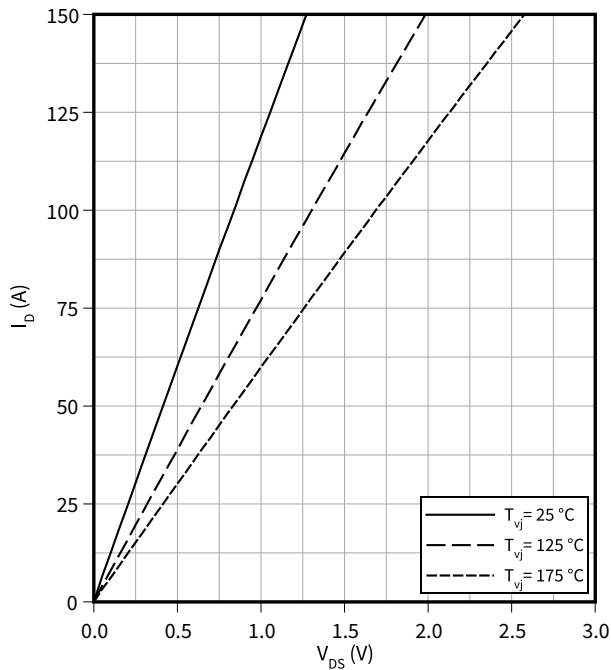
$R_{Gon} = 10\text{ }\Omega$, $I_D = 75\text{ A}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$



7 Characteristics diagrams

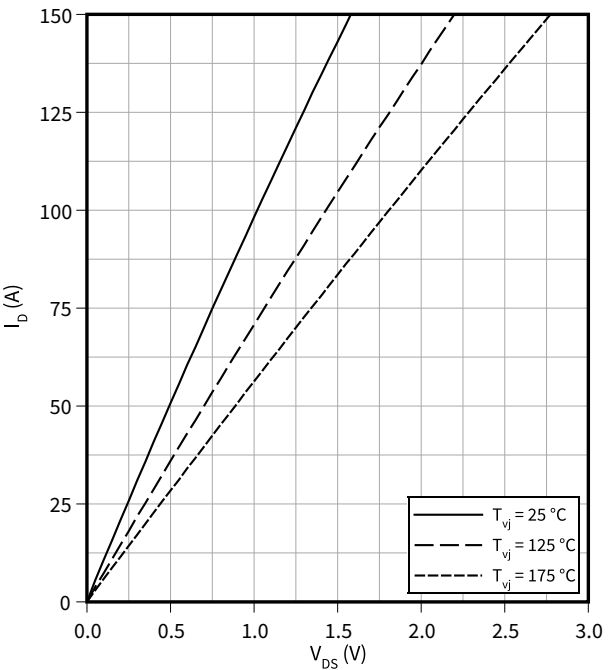
Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$
 $V_{GS} = 18\text{ V}$



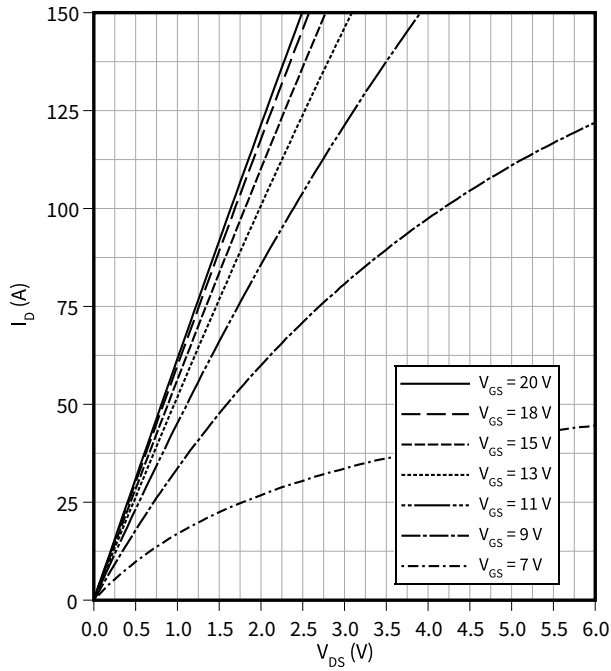
Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$
 $V_{GS} = 15\text{ V}$



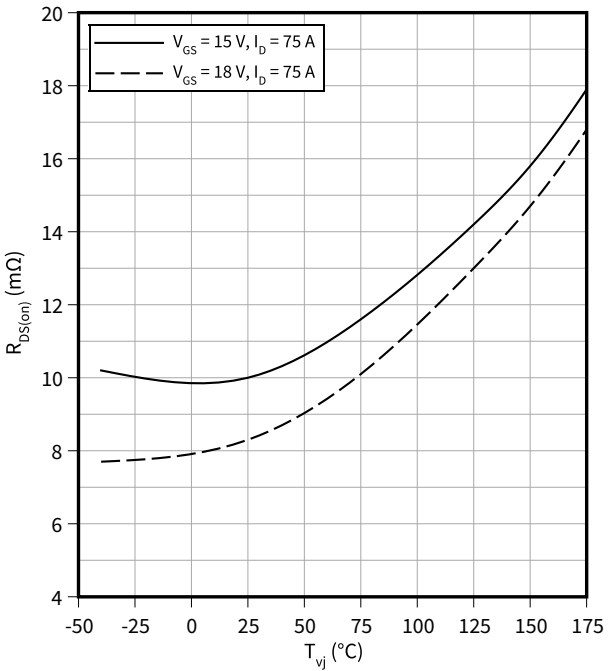
Output characteristic field (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ °C}$



Drain source on-resistance (typical), MOSFET, T3 / T4

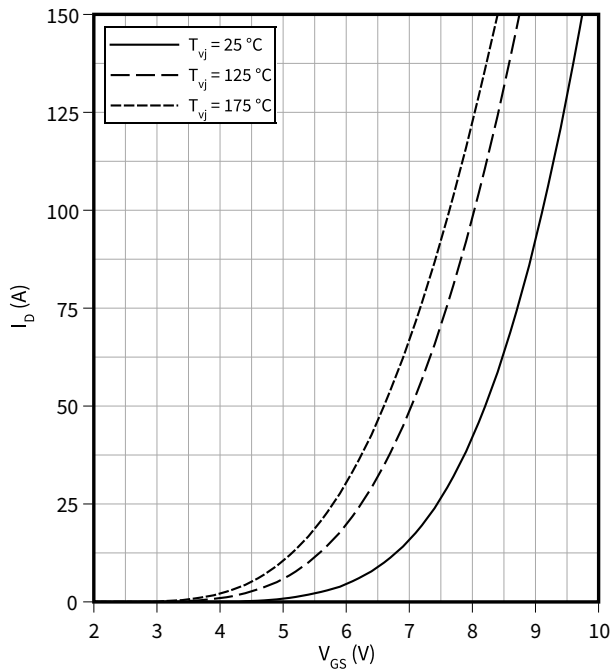
$R_{DS(on)} = f(T_{vj})$



7 Characteristics diagrams

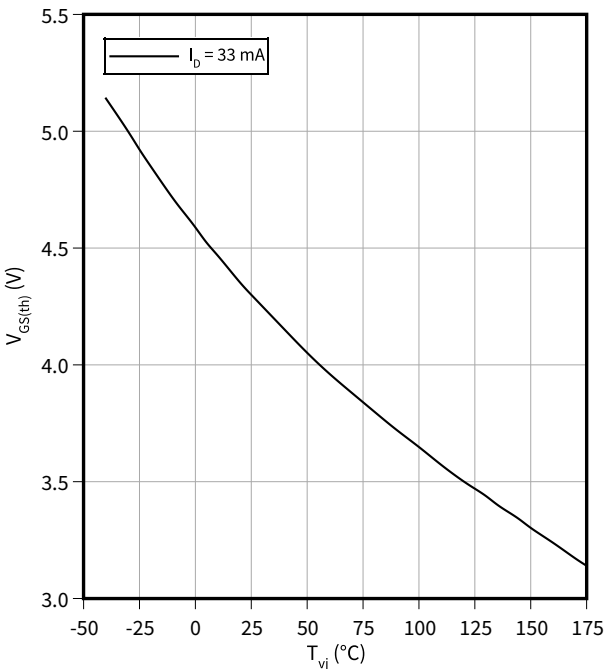
Transfer characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$



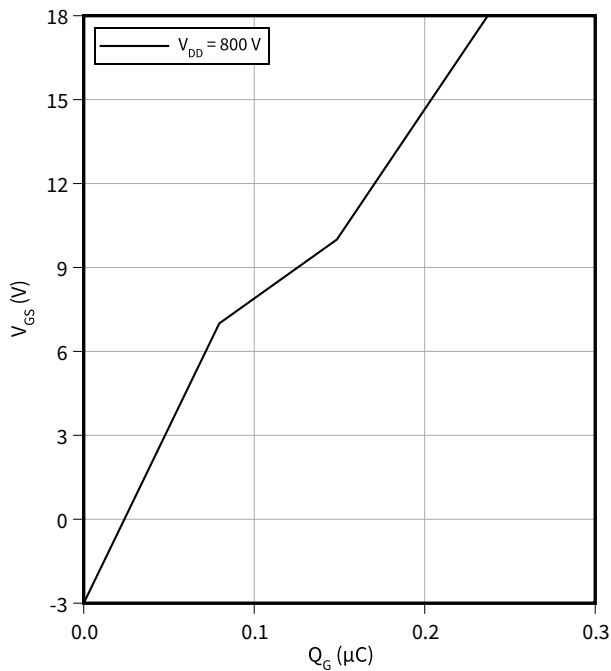
Gate-source threshold voltage (typical), MOSFET, T3 / T4

$V_{GS(th)} = f(T_{vj})$
 $V_{GS} = V_{DS}$



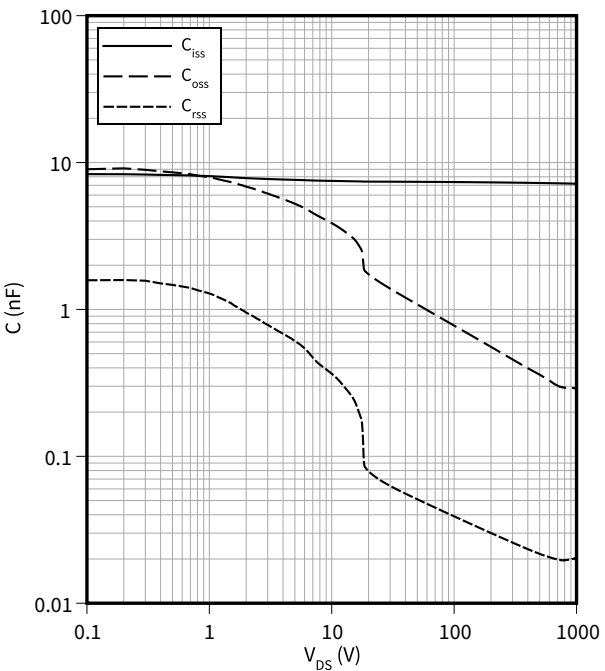
Gate charge characteristic (typical), MOSFET, T3 / T4

$V_{GS} = f(Q_G)$
 $I_D = 75\text{ A}, T_{vj} = 25\text{ °C}$



Capacity characteristic (typical), MOSFET, T3 / T4

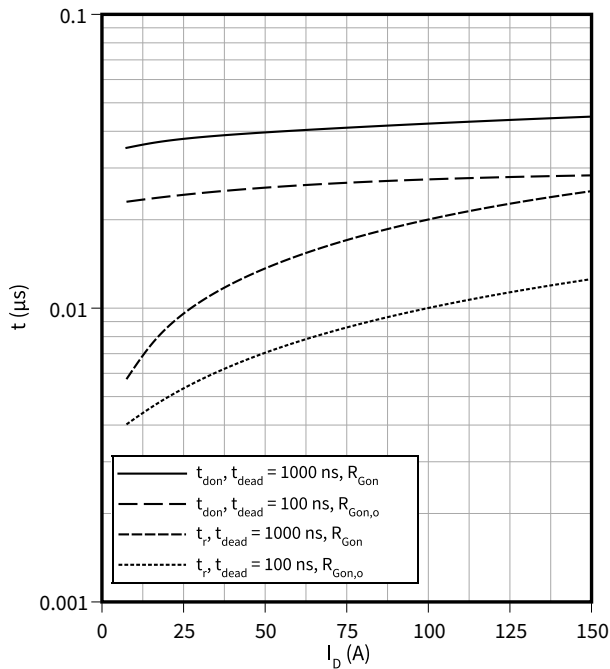
$C = f(V_{DS})$
 $f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{GS} = 0\text{ V}$



7 Characteristics diagrams

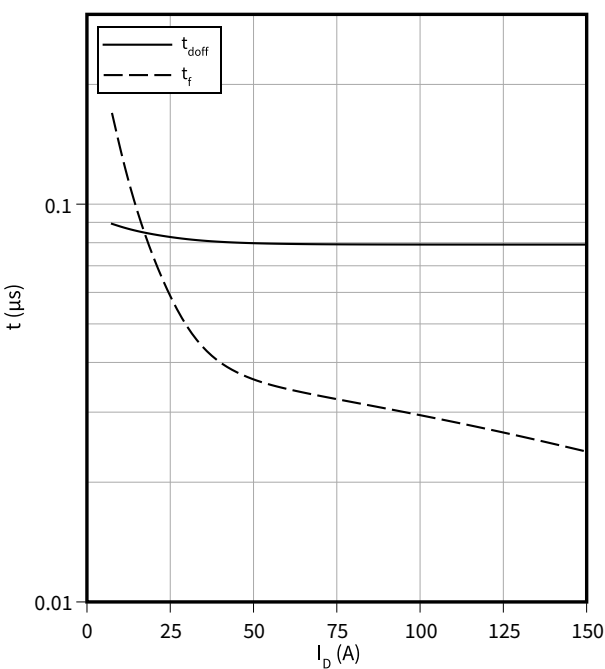
Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$
 $V_{DD} = 800\text{ V}$, $R_{Gon} = 5.6\ \Omega$, $R_{Gon,o} = 0\ \Omega$, $T_{vj} = 175\text{ }^\circ\text{C}$,
 $V_{GS} = -3/18\text{ V}$



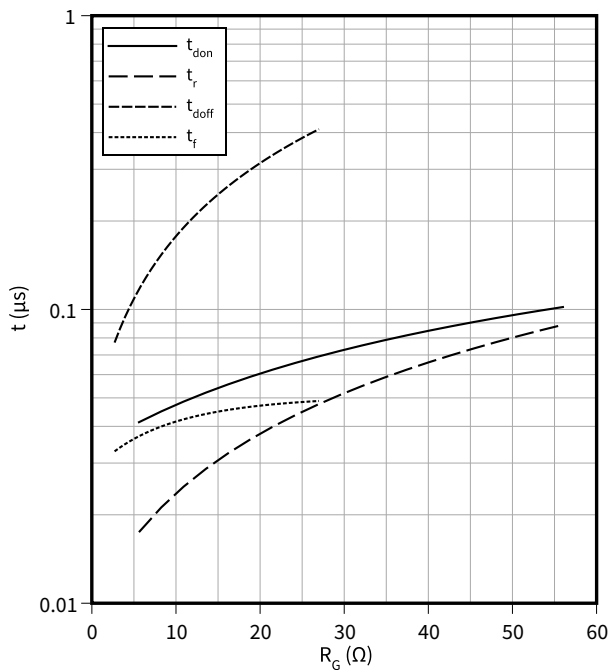
Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$
 $R_{Goff} = 2.7\ \Omega$, $V_{DD} = 800\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



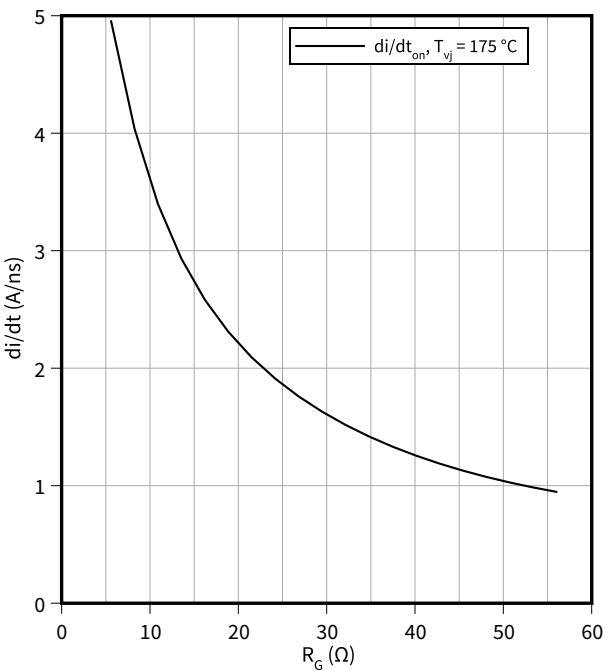
Switching times (typical), MOSFET, T3 / T4

$t = f(R_G)$
 $V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $T_{vj} = 175\text{ }^\circ\text{C}$,
 $V_{GS} = -3/18\text{ V}$



Current slope (typical), MOSFET, T3 / T4

$di/dt = f(R_G)$
 $V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$

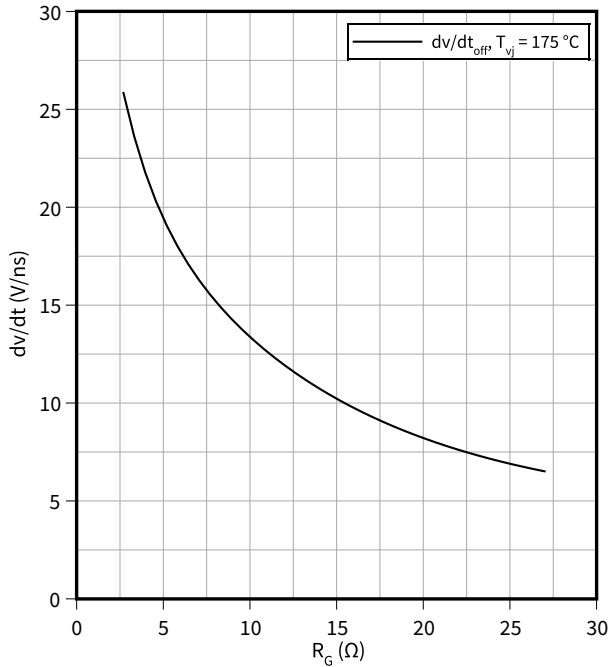


7 Characteristics diagrams

Voltage slope (typical), MOSFET, T3 / T4

$dv/dt = f(R_G)$

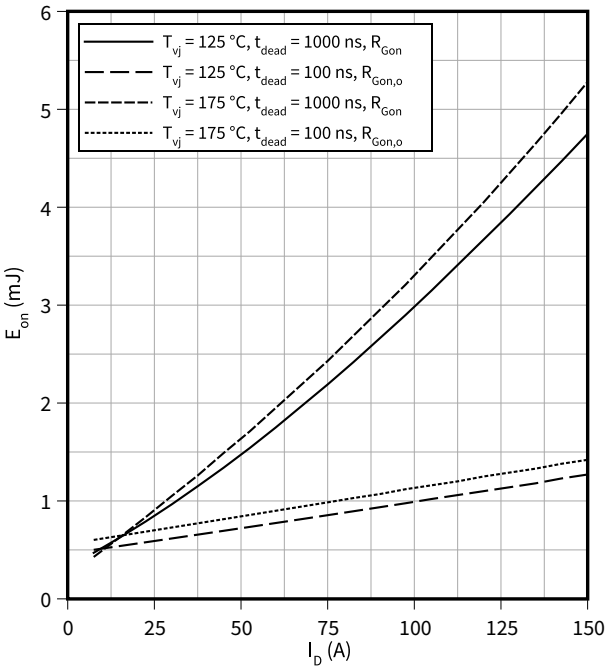
$V_{DD} = 800\text{ V}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(I_D)$

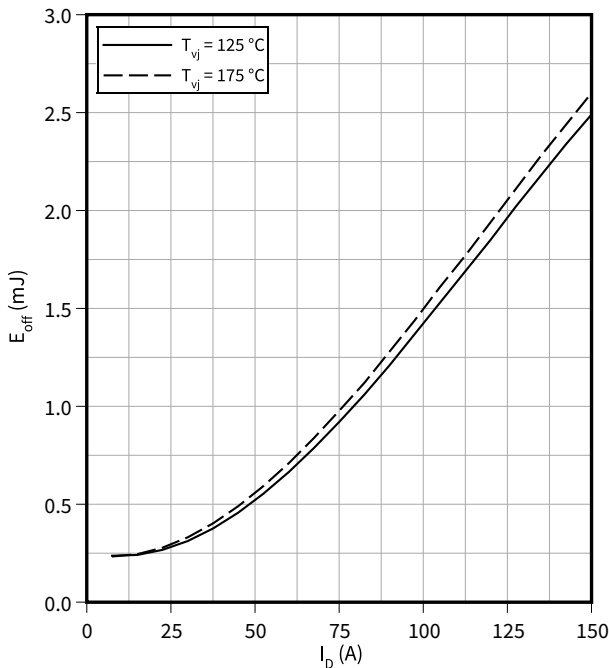
$V_{DD} = 800\text{ V}$, $R_{Gon} = 5.6\text{ Ω}$, $R_{Gon,o} = 0\text{ Ω}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T3 / T4

$E_{off} = f(I_D)$

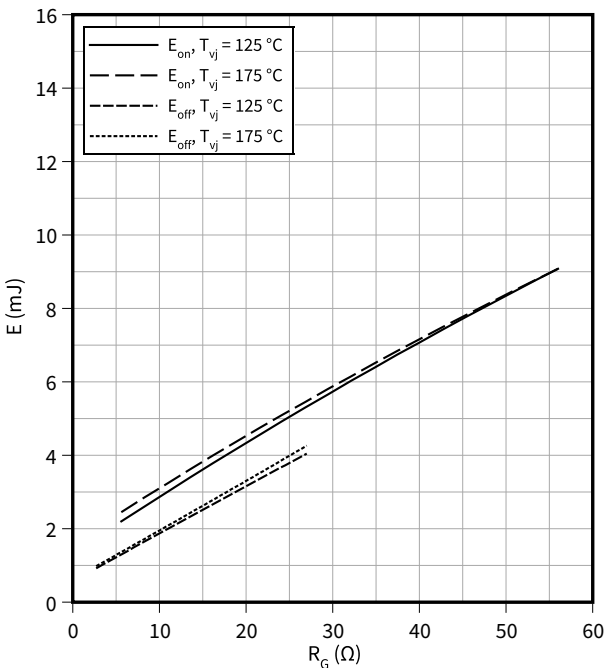
$R_{Goff} = 2.7\text{ Ω}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET, T3 / T4

$E = f(R_G)$

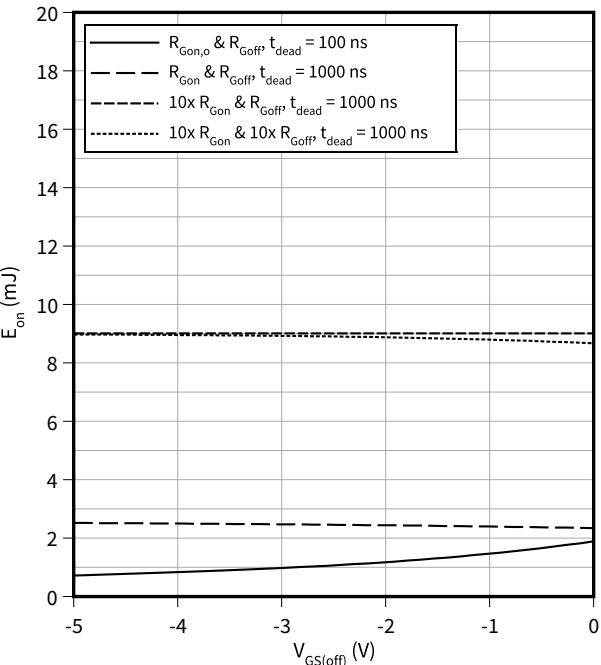
$V_{DD} = 800\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 75\text{ A}$, $V_{GS} = -3/18\text{ V}$



7 Characteristics diagrams

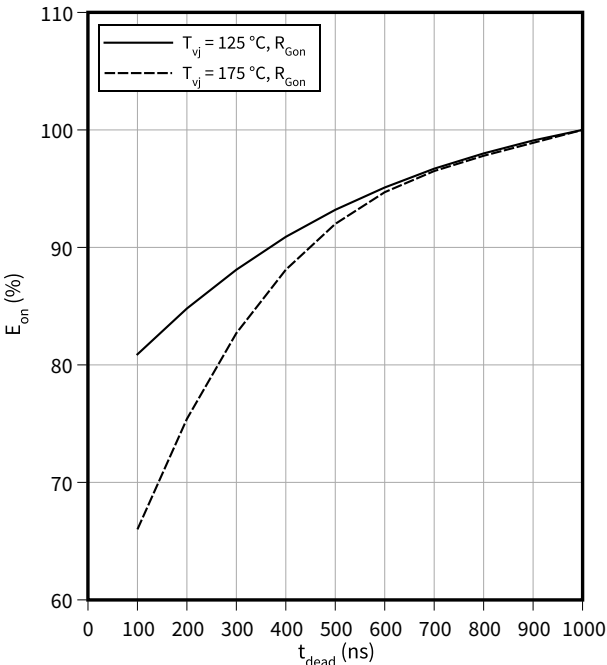
Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(V_{GS(off)})$
 $R_{Goff} = 2.7 \Omega$, $V_{DD} = 800 \text{ V}$, $R_{Gon} = 5.6 \Omega$, $V_{GS(on)} = 18 \text{ V}$,
 $I_D = 75 \text{ A}$, $R_{Gon,0} = 0 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$



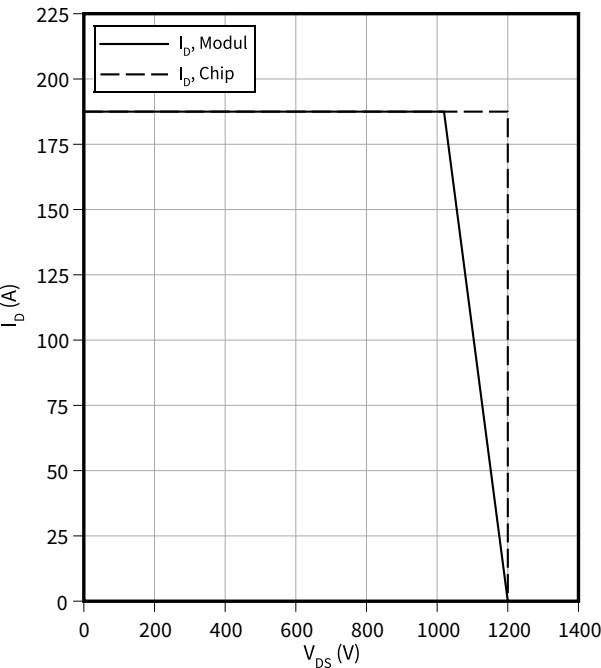
Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(t_{dead})$
 $R_{Gon} = 5.6 \Omega$, $I_D = 75 \text{ A}$, $V_{DD} = 800 \text{ V}$, $V_{GS} = -3/18 \text{ V}$



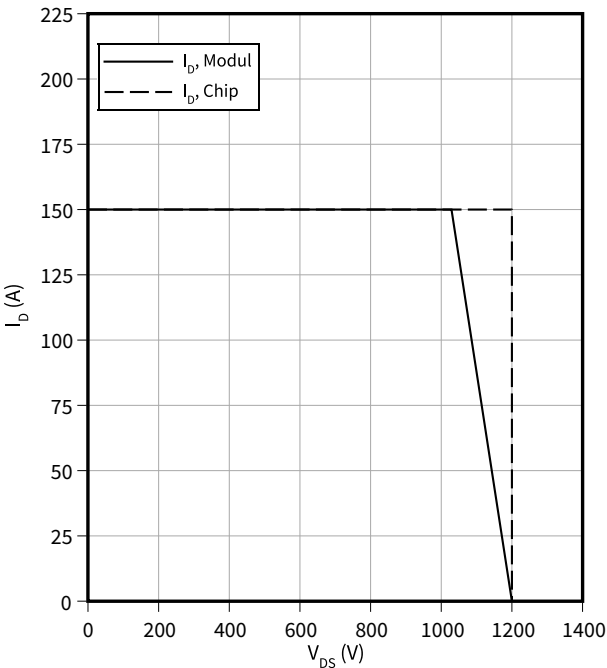
Reverse bias safe operating area (RBSOA), MOSFET, T3 / T4

$I_D = f(V_{DS})$
 $R_{Goff} = 3.6 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GS} = -3/18 \text{ V}$



Reverse bias safe operating area (RBSOA), MOSFET, T3 / T4

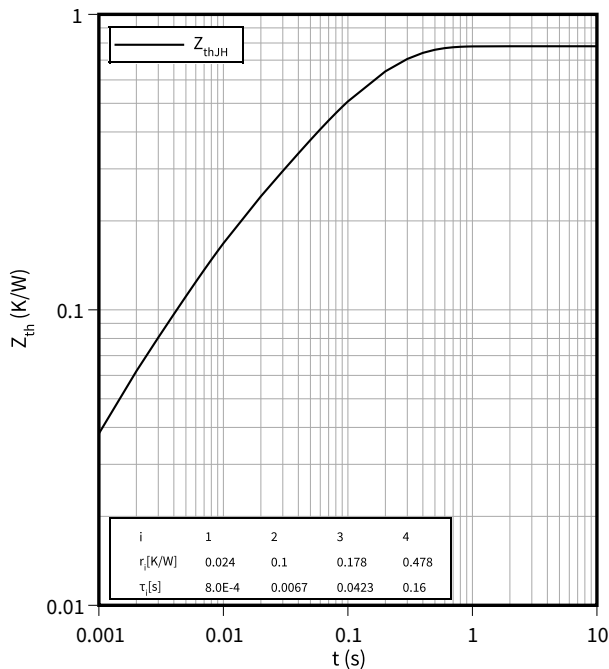
$I_D = f(V_{DS})$
 $R_{Goff} = 2.7 \Omega$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GS} = -3/18 \text{ V}$



7 Characteristics diagrams

Transient thermal impedance, MOSFET, T3 / T4

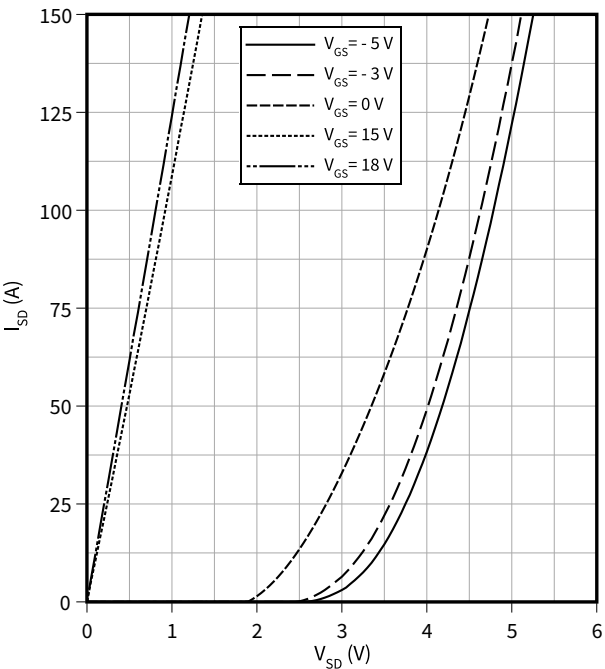
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T3 / T4

$I_{SD} = f(V_{SD})$

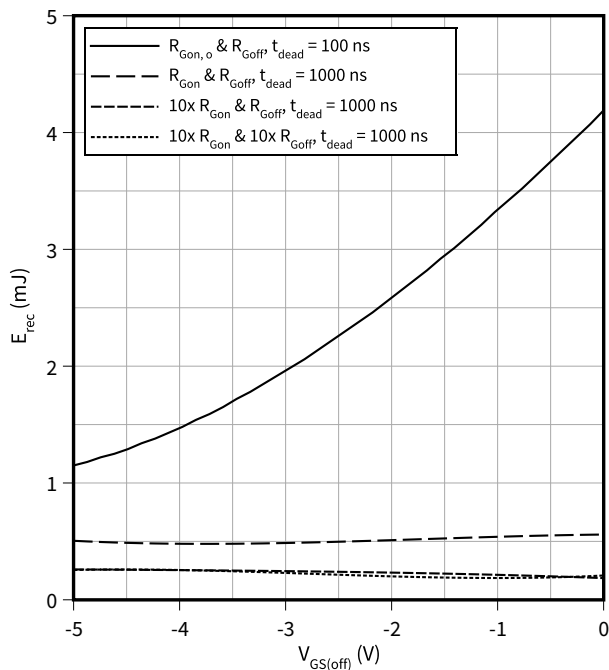
$T_{vj} = 25\text{ }^{\circ}\text{C}$



Switching losses body diode (typical), MOSFET, T3 / T4

$E_{rec} = f(V_{GS(off)})$

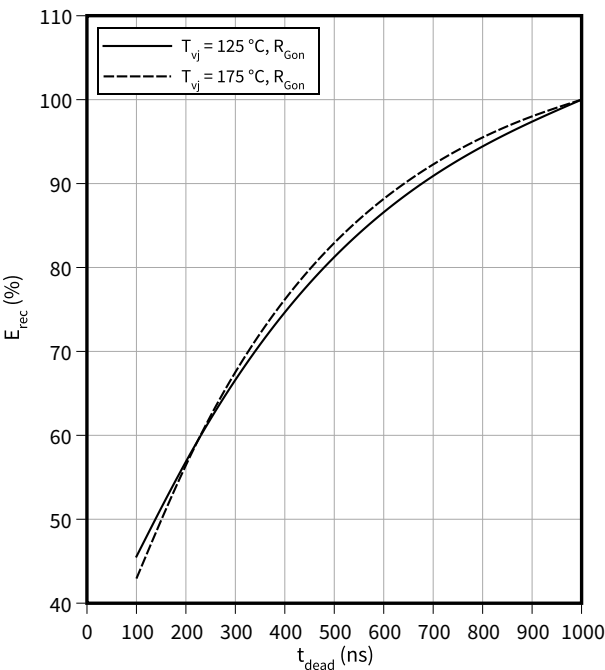
$R_{Goff} = 2.7\text{ }\Omega$, $R_{Gon} = 5.6\text{ }\Omega$, $V_{GS(on)} = 18\text{ V}$, $I_{SD} = 75\text{ A}$,
 $R_{Gon,o} = 0\text{ }\Omega$, $V_{DD} = 800\text{ V}$, $T_{vj} = 175\text{ }^{\circ}\text{C}$



Switching losses body diode (typical), MOSFET, T3 / T4

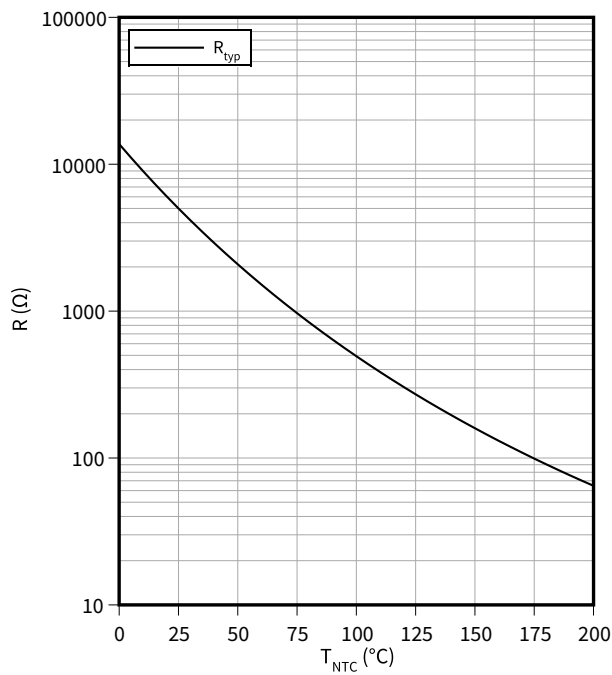
$E_{rec} = f(t_{dead})$

$R_{Gon} = 5.6\text{ }\Omega$, $I_D = 75\text{ A}$, $V_{DD} = 800\text{ V}$, $V_{GS} = -3/18\text{ V}$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



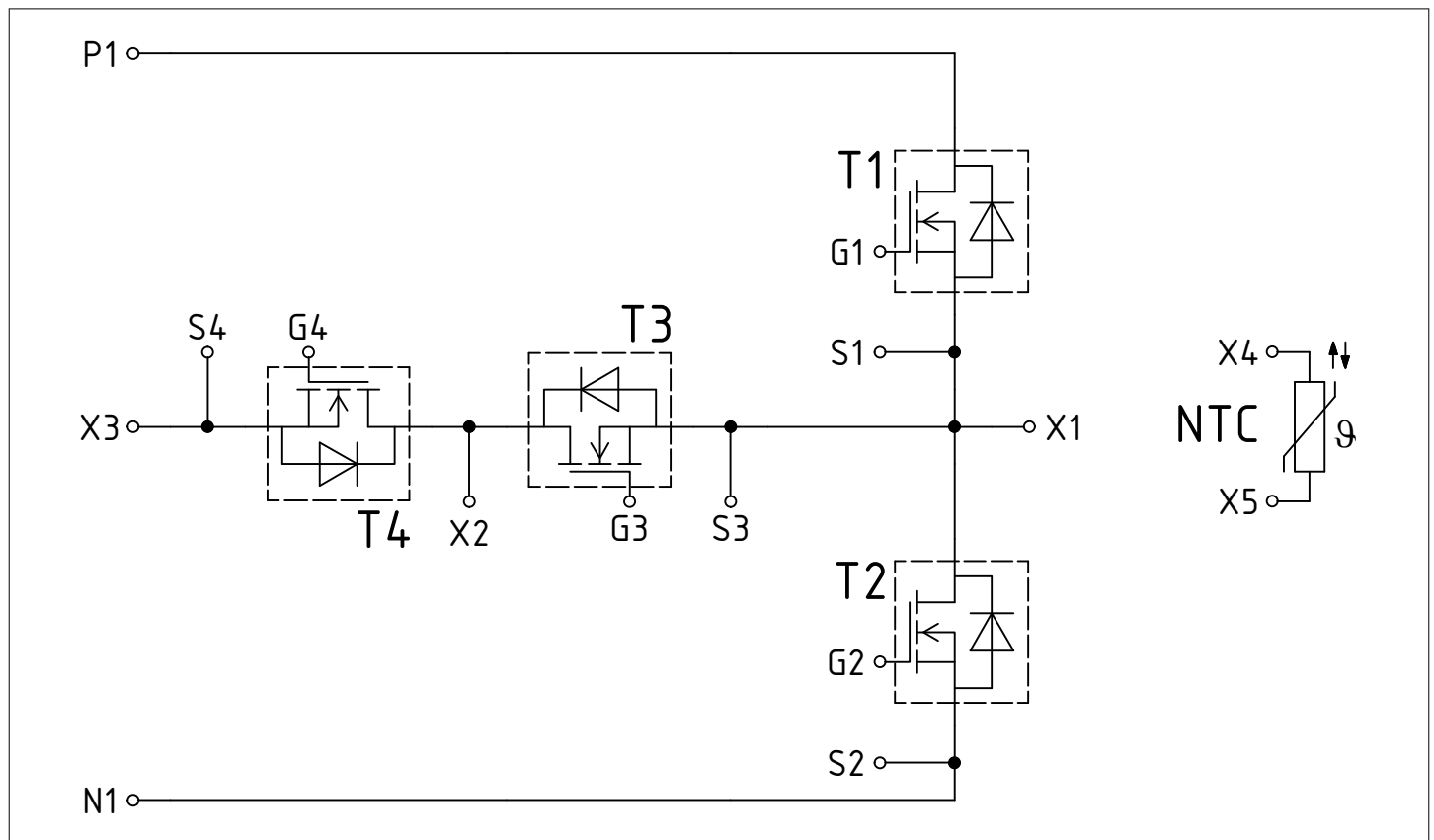


Figure 1

9 Package outlines

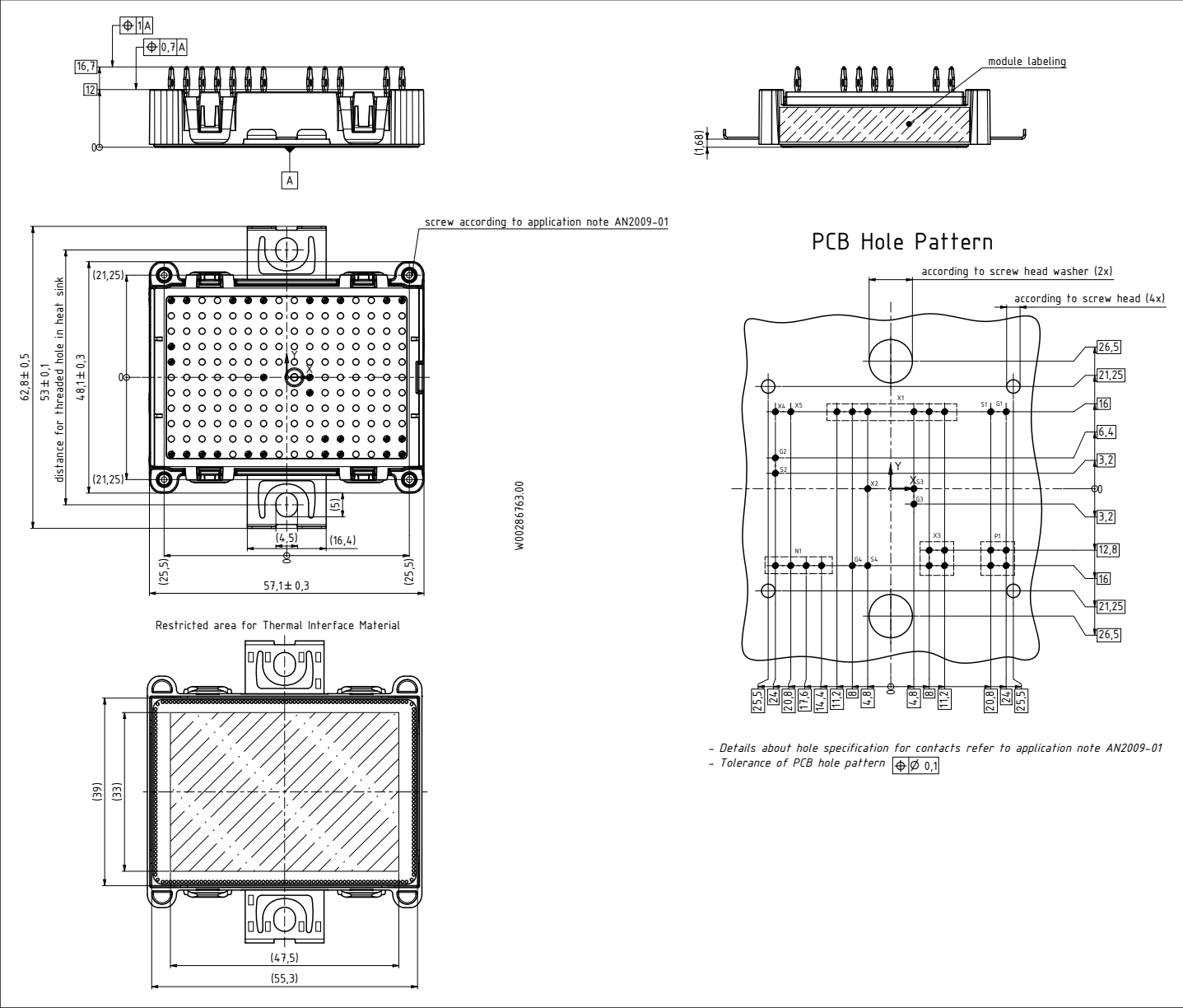


Figure 2

10 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3



Revision history

Revision history

Document revision	Date of release	Description of changes
0.10	2025-07-01	Preliminary datasheet
1.00	2026-03-04	Final Datasheet

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